

EFFICIENCY OF INTERACTION OF INTERSTITIAL
CARBON WITH OXYGEN, TIN,
AND SUBSTITUTION CARBON
IN IRRADIATED SILICON

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S u m m a r y

The infrared Fourier spectroscopy technique is used for the investigation of the efficiency of interaction of interstitial carbon with the basic technological impurities in silicon, oxygen and substitution carbon, as well as with an isoelectronic impurity, tin. It is shown that the probabilities of the interaction of interstitial carbon with interstitial oxygen and substitution carbon are close. It is found that interstitial carbon in tin-doped Si is less thermostable than that in Si, and the temperature of its complete annealing gradually decreases with increasing the tin concentration. It is shown that the probability of the interaction of interstitial carbon with tin exceeds the probability of its interaction with oxygen and on-site carbon by a factor of ~ 2.3 .